

SILICON TRANSISTOR 2SC2721

NPN SILICON EPITAXIAL TRANSISTOR FOR HIGH-FREQUENCY AMPLIFIERS AND MID-SPEED SWITCHING

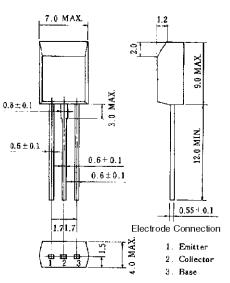
FEATURES

- · Complementary transistor with 2SA1154
- High P_{T} in small dimension and high voltage $P_{T}=1 \ W, \ V_{CEO}=60 \ V$

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	60	V
Collector to emitter voltage	VCEO	60	V
Emitter to base voltage	Vebo	5.0	V
Collector current (DC)	IC(DC)	0.7	Α
Collector current (pulse)	IC(pulse)*	1.0	Α
Total power dissipation	P⊤	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

PACKAGE DRAWING (UNIT: mm)



* PW \leq 10 ms, duty cycle \leq 50%

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$			100	nA
Emitter cutoff current	Іево	V _{EB} = 5.0 V, Ic = 0			100	nA
DC current gain	hfe1	$V_{CE} = 1.0 \text{ V}, \text{ Ic} = 0.1 \text{ A}^{+}$	90	200	400	
DC current gain	hfe2	$V_{\text{CE}}=1.0$ V, Ic = 0.5 A *	50	150		
DC base voltage	VBE	$V_{CE} = 6.0 \text{ V}, \text{ Ic} = 10 \text{ mA}$	600	635	700	mV
Collector saturation voltage	V _{CE(sat)}	$I_{C} = 0.5 \text{ A}, I_{B} = 50 \text{ mA}^{*}$		0.12	0.35	V
Base saturation voltage	V _{BE(sat)}	$Ic = 0.5 A$, $I_B = 50 mA$ *		0.90	1.2	V
Output capacitance	Cob	$V_{CB} = 6.0 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$		13		pF
Gain bandwidth product	fт	Vce = 6.0 V, Ie = -10 mA		110		MHz
Turn-on time	ton	Refer to the test circuit.		60		ns
Storage temperature	tstg			600		ns
Turn-off time	t _{off}			650		ns

* Pulse test PW \leq 350 μ s, duty cycle \leq 2% per pulsed

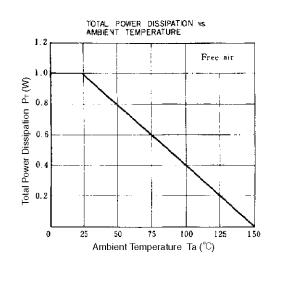
hfe CLASSIFICATION

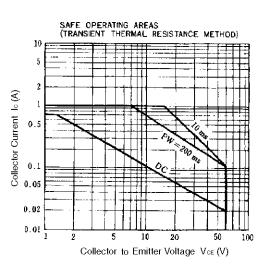
Marking	MA	LA	KA
h _{FE1}	90 to 180	135 to 270	200 to 400

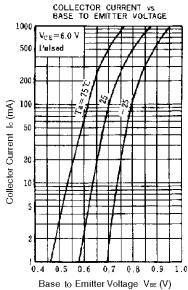
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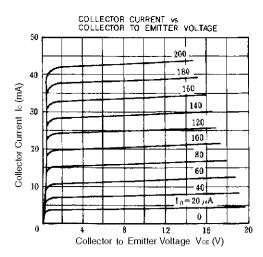
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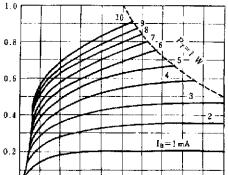
TYPICAL CHARACTERISTICS (Ta = 25°C)



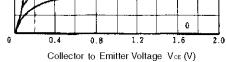


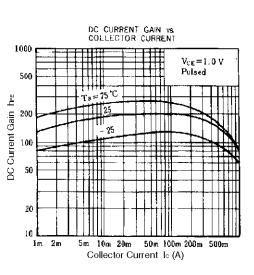






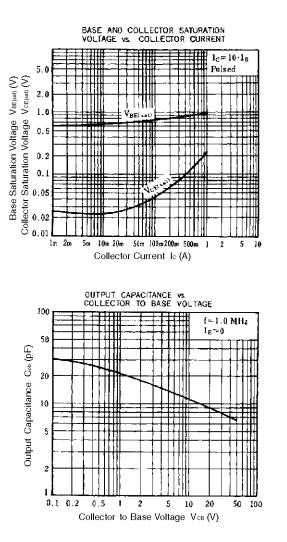
COLLECTOR CURRENT VS COLLECTOR TO EMITTER VOLTAGE

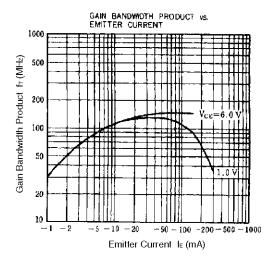




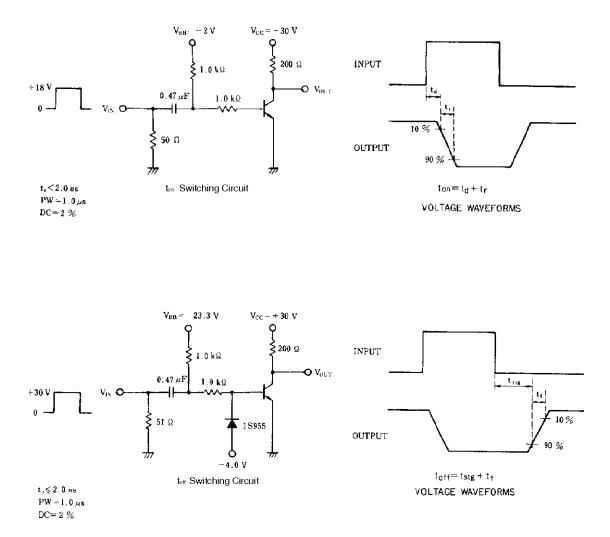
Collector Current Ic (A)

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SWITCHING TIME TEST CIRCUIT



[MEMO]

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